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L5: Entry 28 of 49

File: JPAB

Jan 25, 2002

PUB-NO: JP02002026389A

DOCUMENT-IDENTIFIER: JP 2002026389 A

TITLE: METHOD FOR MANUFACTURING P-TYPE GALLIUM NITRIDE COMPOUND SEMICONDUCTOR,
METHOD FOR MANUFACTURING GALLIUM NITRIDE COMPOUND SEMICONDUCTOR LIGHT EMITTING
ELEMENT AND GALLIUM NITRIDE COMPOUND SEMICONDUCTOR LIGHT EMITTING ELEMENT

PUBN-DATE: January 25, 2002

INVENTOR-INFORMATION:

NAME

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MIKI, HISAYUKI

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OSHIMA, MASAHARU

FUJIOKA, HIROSHI

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SHOWA DENKO KK

APPL-NO: JP2000207701

APPL-DATE: July 10, 2000

INT-CL (IPC): H01 L 33/00; C23 C 16/34; H01 L 21/205; H01 L 21/324

ABSTRACT:

PROBLEM TO BE SOLVED: To enable p-type conduction without deterioration of a crystal of a light emitting layer and without contamination at a low cost and realize a good ohmic contact with an electrode.

SOLUTION: A method for manufacturing a p-type gallium nitride compound semiconductor comprises a first step of manufacturing a gallium nitride compound semiconductor layer 3 in which a p-type impurity is added, a second step of manufacturing a catalytic layer 7 made of a metal or the like on the layer 3, and a third step of heat treating the layer 3 in a state in which the layer 7 is attached.

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L5: Entry 32 of 49

File: JPAB

Oct 8, 1999

PUB-NO: JP411274567A

DOCUMENT-IDENTIFIER: JP 11274567 A

TITLE: METHOD FOR FORMING ELECTRODE OF SEMICONDUCTOR ELEMENT

PUBN-DATE: October 8, 1999

INVENTOR-INFORMATION:

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SHOWA DENKO KK

APPL-NO: JP10079681

APPL-DATE: March 26, 1998

INT-CL (IPC): H01 L 33/00

ABSTRACT:

PROBLEM TO BE SOLVED: To control the Ohmic contact of electrodes to a semiconductor by forming a protection layer of at least an element selected from a group of P, As, Sb, S and Se on the surface of a GaN compound semiconductor and laminating an electrode material on the protection layer to form electrodes.

SOLUTION: On a p-type GaN substrate grown by the MOCVD method, an As protection layer is formed in an MBE apparatus different from the one used for this growth, Pd electrodes are formed on the protection layer, and a pattern of pairs of planar electrodes 13 and dot electrodes 14 for measuring the current-voltage characteristic of the contact between the electrode and semiconductor is formed in a sample with the As protection layer. The current-voltage characteristic measured between the electrodes can be regarded as a contact characteristic of the dot electrode 14, resulting in that the current-voltage characteristic 12 shows an Ohmic property.

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WEST Search History

DATE: Monday, June 09, 2003

<u>Set Name</u> side by side	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u> result set
<i>DB=USPT,PGPB,JPAB,EPAB,DWPI,TDBD; PLUR=YES; OP=OR</i>			
L9	17 and 18	2	L9
L8	p-gan	398	L8
L7	14 and 16	675	L7
L6	catalys\$4	684263	L6
L5	13 and 14	49	L5
L4	(gallium adj nitride)or gan	14485	L4
L3	okuyama.inv.	9392	L3
L2	20020175341	2	L2
L1	20020175341	2	L1

END OF SEARCH HISTORY